



Description

JMT N-channel Enhancement Mode Power MOSFET

Features

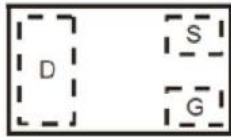
- 20V, 0.75A
 $R_{DS(ON)} < 165m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} < 260m\Omega @ V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired
- ESD Protected: 2KV

Application

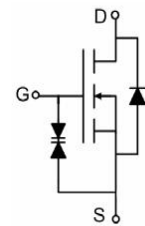
- Load Switch
- PWM Application
- Power management



DFN1006-3L top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
34K	JMTD3134K	TAPING	DFN1006-3L	7inch	10000	400000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 10	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	0.75
		$T_A = 100^\circ C$	0.5
I_{DM}	Pulsed Drain Current <small>note1</small>	3	A
P_D	Power Dissipation	$T_A = 25^\circ C$	0.15
$R_{\theta JA}$	Thermal Resistance, Junction to Case	833	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V,	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±10V	-	-	±10	uA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.7	1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =4.5V, I _D =0.5A	-	125	240	mΩ
		V _{GS} =2.5V, I _D =0.4A	-	185	280	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	60	-	pF
C _{oss}	Output Capacitance		-	22	-	pF
C _{riss}	Reverse Transfer Capacitance		-	12	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =0.75A, V _{GS} =4.5V	-	1	-	nC
Q _{gs}	Gate-Source Charge		-	0.28	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	0.22	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V	-	2	-	ns
t _r	Turn-on Rise Time		-	19	-	ns
t _{d(off)}	Turn-off Delay Time		-	10	-	ns
t _f	Turn-off Fall Time		-	23	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	0.75	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	3	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =0.75A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

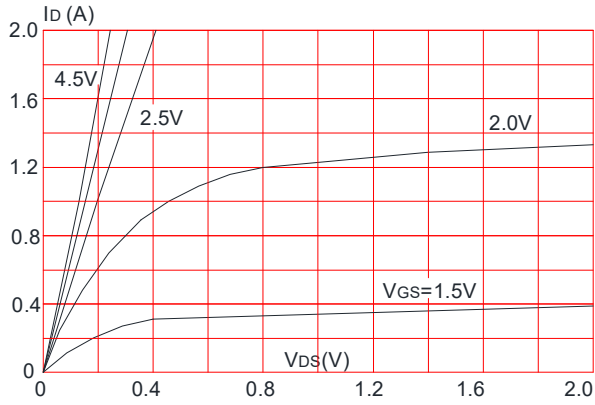


Figure 2: Typical Transfer Characteristics

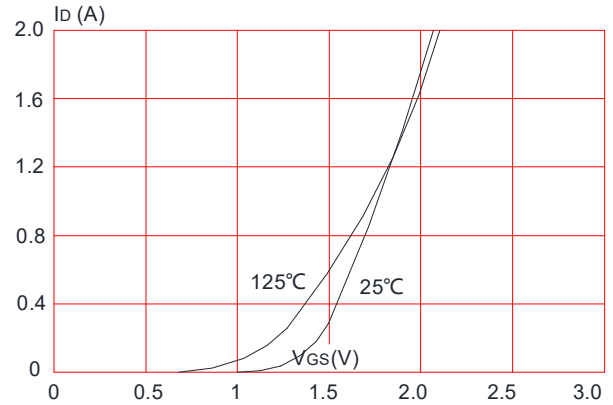


Figure 3: On-resistance vs. Drain Current

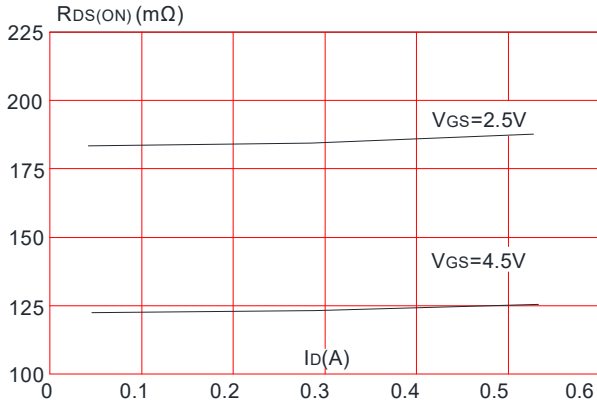


Figure 4: Body Diode Characteristics

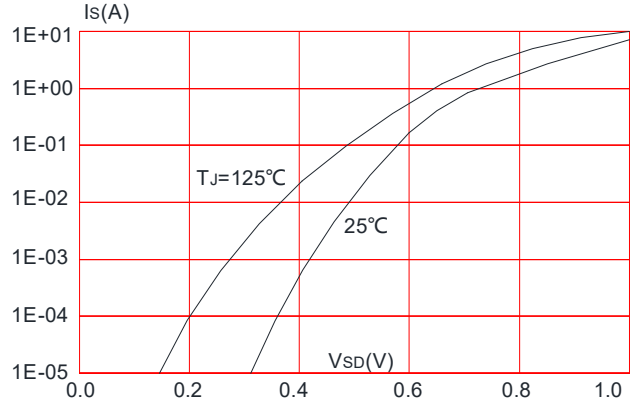


Figure 5: Gate Charge Characteristics

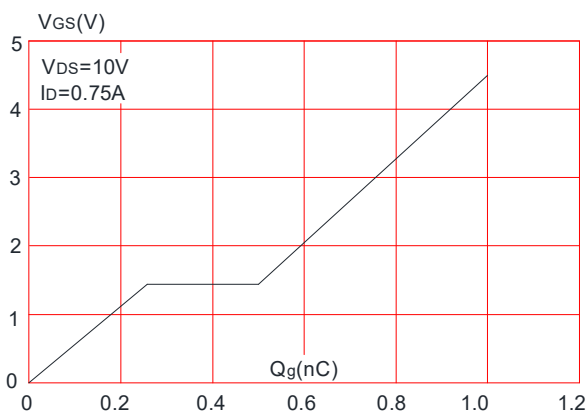


Figure 6: Capacitance Characteristics

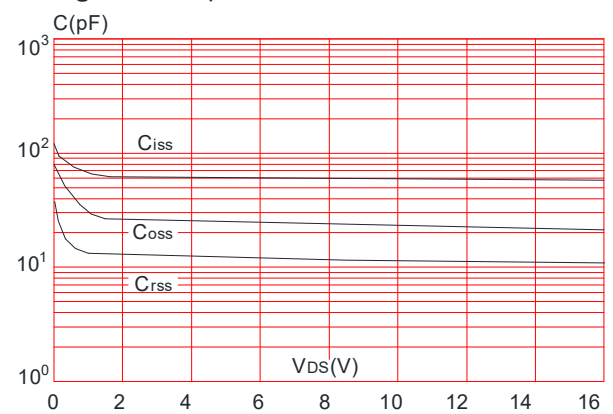




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

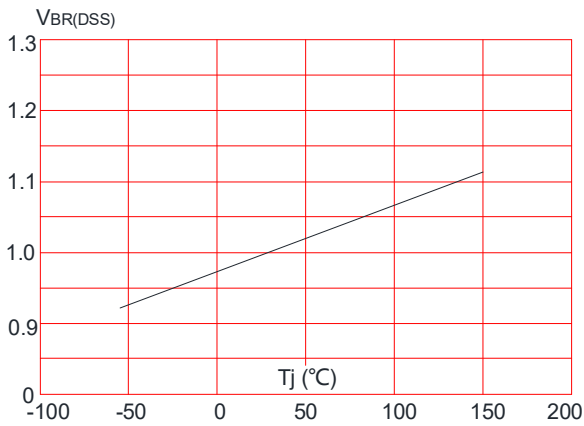


Figure 8: Normalized on Resistance vs. Junction Temperature

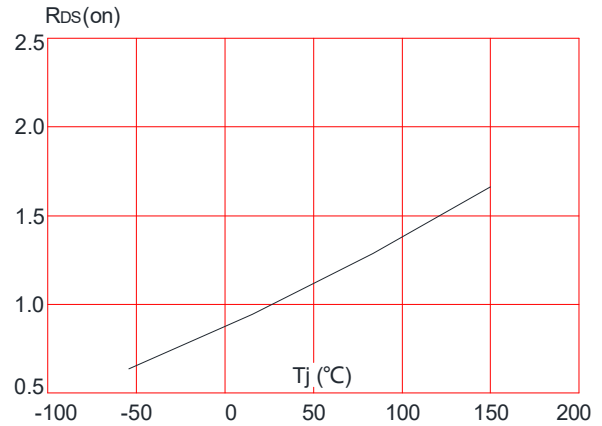


Figure 9: Maximum Safe Operating Area

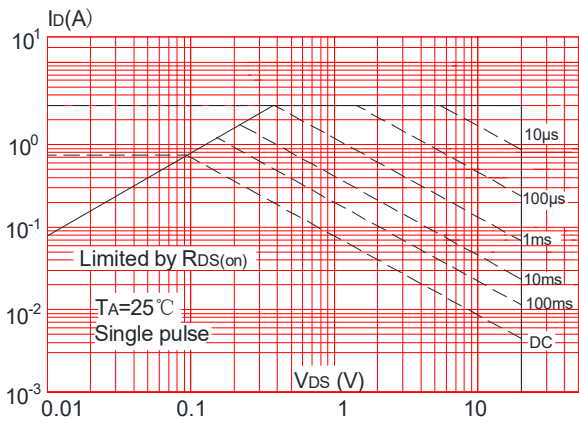


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

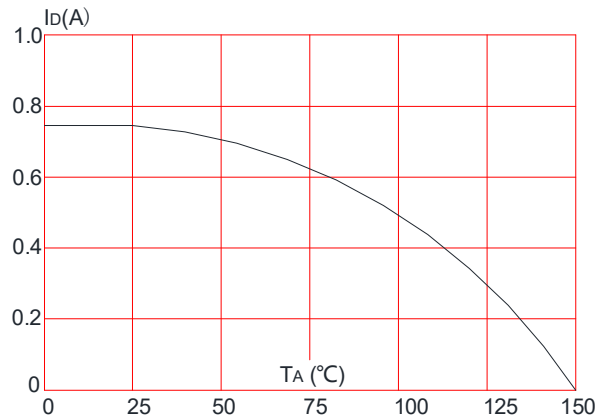
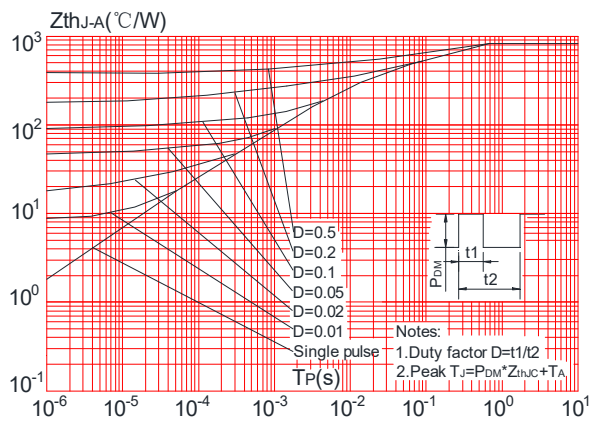


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit



Figure1:Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveforms

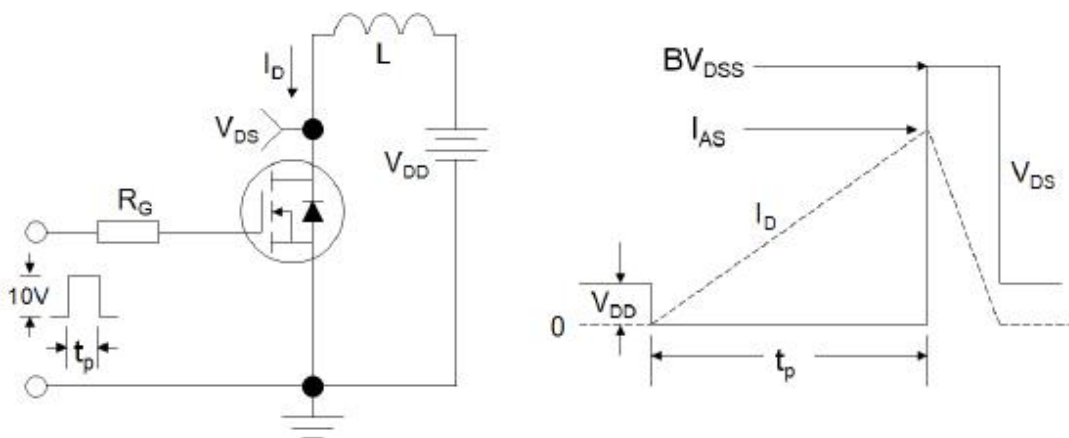
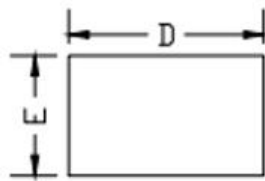
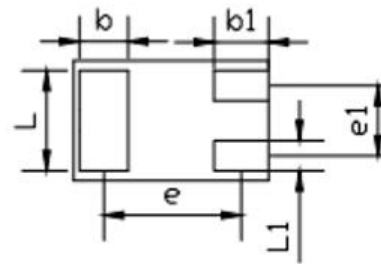


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

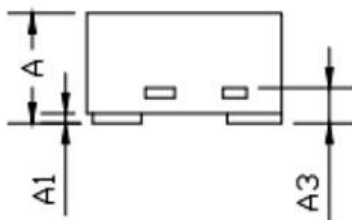
Package Mechanical Data-DFN1006-3L



TOP VIEW



BOTTOM VIEW



SIDE VIEW

COMMON DIMENSION (MM)			
PKG	DFN1006		
REF.	MIN.	NDM.	MAX
A	>0.4	-	0.50
A1	0.00	-	0.05
A3	0.127REF.		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.20	0.25	0.30
b1	0.20	0.30	0.40
L	0.45	0.50	0.55
L1	0.10	0.15	0.20
e	0.675		
e1	0.35		

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